

Analysis of barrier inhomogeneities of P-type Al/4H-SiC Schottky barrier diodes

Ziko, Mehadi Hasan; Koel, Ants; Rang, Toomas; Toompuu, Jana Silicon Carbide and Related Materials 2019 : 18th International Conference on Silicon Carbide and Related Materials 2019 (ICSCRM 2019), Kyoto, Japan, September 29 - October 4, 2019 2020 / p. 960-972 <https://doi.org/10.4028/www.scientific.net/MSF.1004.960> [Conference proceedings at Scopus](#) [Article at Scopus](#)

Analysis of deep level centers in GaAs pin-diode structures

Korolkov, Oleg; Toompuu, Jana; Rang, Toomas Elektronika ir elektrotehnika = Electronics and electrical engineering 2013 / [4 p.] : ill

Analysis of deep level spectrum in GaAs p+-p-i-n-n+ structures

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Change in the parameters of electron-irradiated 4H-SiC Schottky diodes as a function of the time during low-temperature isothermal annealing

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Comparative characteristics of diffusion-welded high-voltage stacks and connected in series Schottky diodes

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Comparative investigation of the graphene-on-silicon carbide and CVD graphene as a basis for biosensor application

Sleptšuk, Natalja; Lebedev, Alexander A.; Eliseyev, Ilya; Korolkov, Oleg; Toompuu, Jana; Land, Raul; Mikli, Valdek; Zubov, Alexander; Rang, Toomas Modern Materials and Manufacturing 2019 : 12th International DAAAM Baltic Conference and 27th International Baltic Conference BALTMATRIB 2019. Selected, peer reviewed papers from the conference Modern Materials and Manufacturing 2019 (MMM 2019), April 24-26, 2019, Tallinn, Estonia 2019 / p. 185-190 : ill https://www.ester.ee/record=b5235278*est <https://www.scientific.net/KEM.799.185> <https://doi.org/10.4028/www.scientific.net/KEM.799.185> [Conference proceeding at Scopus](#) [Article at Scopus](#)

Comparative results of low temperature annealing of lightly doped n-layers of silicon carbide irradiated by protons and electrons

Kozlovski, Vitali V.; Korolkov, Oleg; Lebedev, Alexander A.; Toompuu, Jana; Sleptšuk, Natalja Silicon Carbide and Related Materials 2019 : 18th International Conference on Silicon Carbide and Related Materials 2019 (ICSCRM 2019), Kyoto, Japan, September 29 - October 4, 2019 2020 / p. 231-236 <https://doi.org/10.4028/www.scientific.net/MSF.1004.231> [Conference Proceedings at Scopus](#) [Article at Scopus](#)

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Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0.9 MeV electrons

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DLTS measurements on 4H-SiC JBS-diodes with boron implanted local p-n junctions

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Low-temperature annealing of lightly doped n-4H-SiC layers after irradiation with fast electrons

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Method of samples preparation intended for research of deep centers in i-, n-, and p-layers of GaAs p⁺-pin-n⁺ structures and result of analysis

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SiC JBS diode symmetrical voltage doubler represented as the diffusion-welded stack

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SIC schottky diode rectifier bridge represented as the diffusion-welded stack

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The specificity of solid-phase interaction of aluminium with silicon carbide in the manufacture of diffusion-welded contacts to semiconductor devices

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